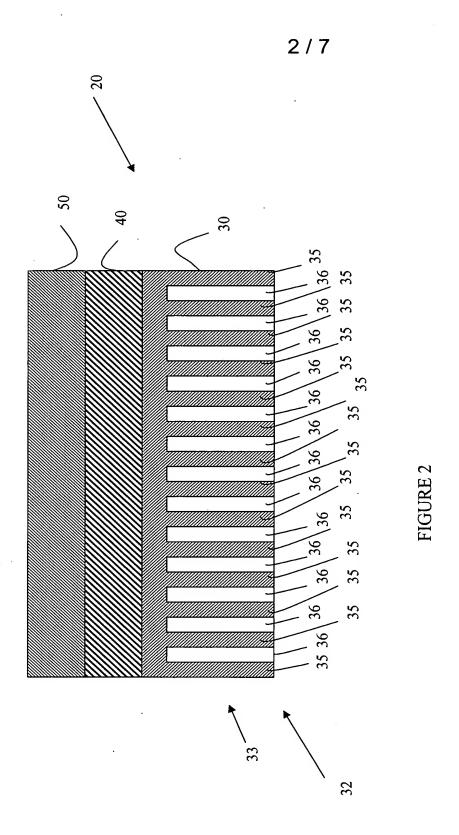
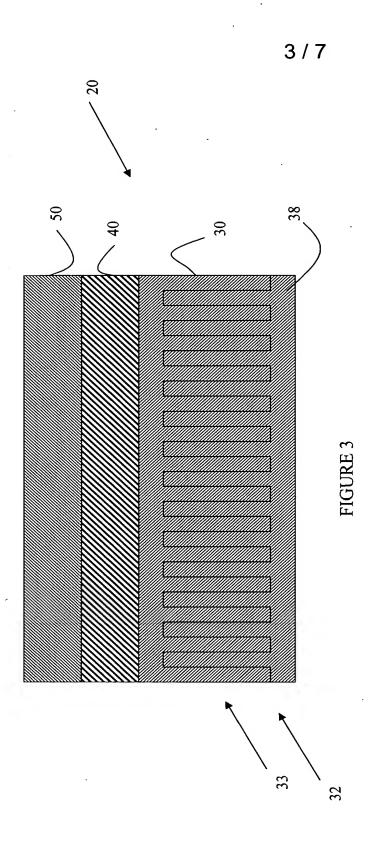


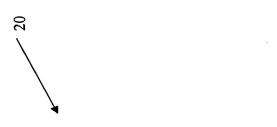
Title: STRAINED SEMICONDUCTOR SUBSTRATE AND PROCESSES THEREFOR Inventor(s): Pelella et al.
Appl. No.: Unknown

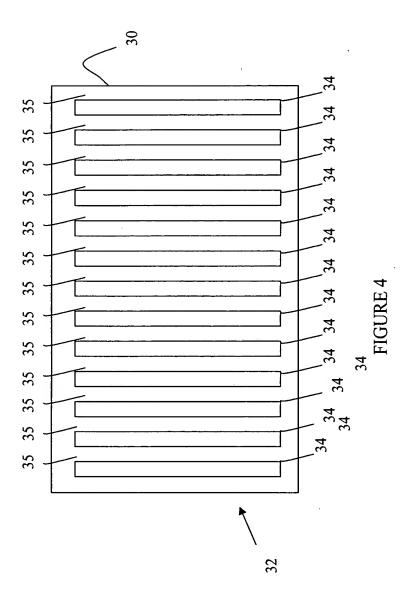


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Appl. No.: Unknown

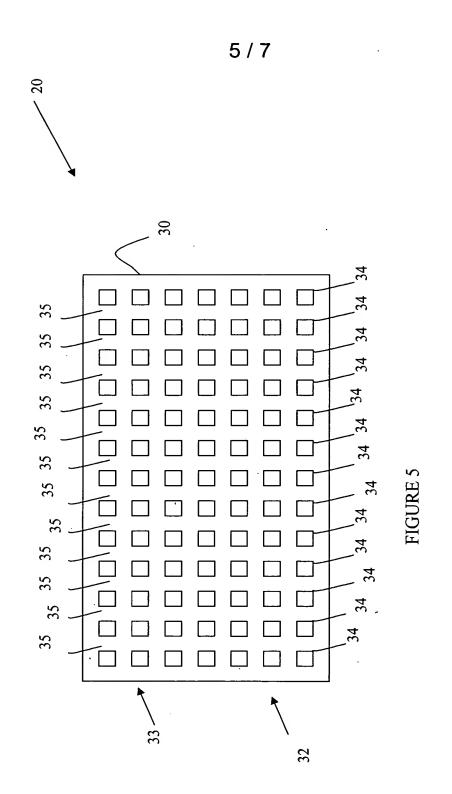




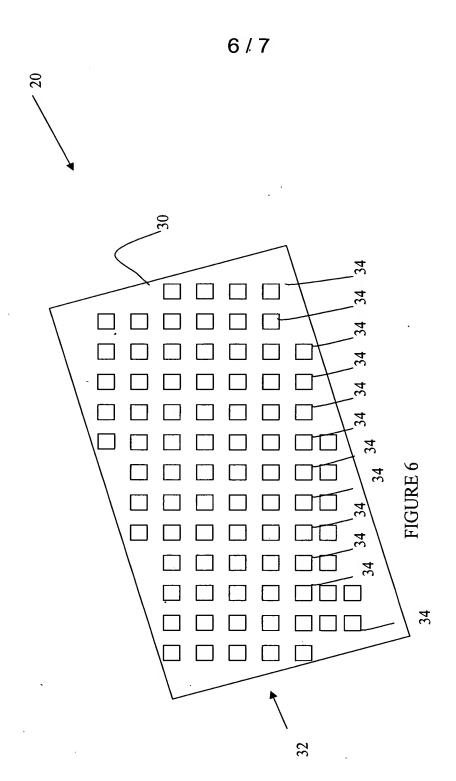




Title: STRAINED SEMICONDUCTOR SÜBSTRATE AND PROCESSES THEREFOR Inventor(s): Pelella et al.
Appl. No.: Unknown



Title: STRAINED SEMICONDUCTOR SUBSTRATE AND PROCESSES THEREFOR Inventor(s): Pelella et al. Appl. No.: Unknown



Title: STRAINED SEMICONDUCTOR SUBSTRATE AND PROCESSES THEREFOR Inventor(s): Pelella et al.
Appl. No.: Unknown

[≈],7/7 Planarize Material Deposit Material in Apertures Between Pillars Etch Trench To Form Pillars FIGURE 7